

isc Thyristors

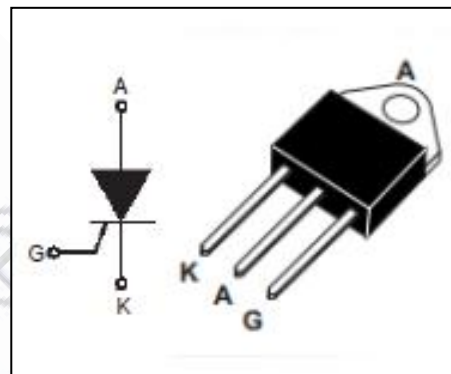
BTW69-600RG

DESCRIPTION

- With TO-3P packaging
- High commutation capability
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

APPLICATIONS

- Switching applications
- Battery charging system
- Uninterruptible power supply
- Variable speed motor drive
- Industrial welding systems
- By pass AC switch


ABSOLUTE MAXIMUM RATINGS($T_a=25^{\circ}\text{C}$)

SYMBOL	PARAMETER		MAX	UNIT
V _{DRM}	Repetitive peak off-state voltage		600	V
V _{RRM}	Repetitive peak reverse voltage		600	V
I _{T(RSM)}	Average on-state current	@T _c =75℃	50	A
I _{TSM}	Surge non-repetitive on-state current	50Hz 60Hz	580 610	A
P _{G(AV)}	Average gate power dissipation (over any 20 ms period) @T _c =125℃		1	W
T _j	Operating junction temperature		-40~125	℃
T _{stg}	Storage temperature		-40~150	℃

ELECTRICAL CHARACTERISTICS ($T_c=25^{\circ}\text{C}$ unless otherwise specified)

SYMBOL	PARAMETER	CONDITIONS	MIN	MAX	UNIT
I_{RRM}	Repetitive peak reverse current	$V_R=V_{\text{RRM}}$ Rated; $T_j=25^{\circ}\text{C}$		10	μA
I_{DRM}	Repetitive peak off-state current	$V_D=V_{\text{DRM}}$ Rated; $T_j=125^{\circ}\text{C}$		5	mA
V_{TM}	On-state voltage	$I_T=100\text{A}; t_p=380\mu\text{s}$		1.9	V
I_{GT}	Gate-trigger current	$V_D=12\text{V}; R_L=33\Omega$		80	mA
V_{GT}	Gate-trigger voltage	$V_D=12\text{V}; R_L=33\Omega$		1.3	V
$R_{\text{th (j-c)}}$	Junction to case	For AC		0.9	$^{\circ}\text{C/W}$